



ON Semiconductor®

FGH40T100SMD

1000 V, 40 A Field Stop Trench IGBT

Features

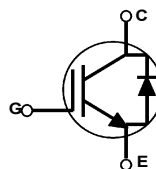
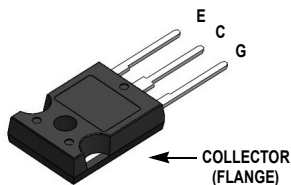
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.9 \text{ V(Typ.) @ } I_C = 40 \text{ A}$
- High Input Impedance
- Fast Switching
- RoHS Compliant

General Description

Using innovative field stop trench IGBT technology, ON Semiconductor new series of field stop trench IGBTs offer the optimum performance for hard switching application such as UPS, welder and PFC applications.

Applications

- UPS, welder, PFC



Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
V_{CES}	Collector to Emitter Voltage	1000	V
V_{GES}	Gate to Emitter Voltage	± 25	V
	Transient Gate to Emitter Voltage	± 30	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	80	A
	Collector Current @ $T_C = 100^\circ\text{C}$	40	A
$I_{CM(1)}$	Pulsed Collector Current @ $T_C = 25^\circ\text{C}$	120	A
I_F	Diode Forward Current @ $T_C = 25^\circ\text{C}$	80	A
	Diode Forward Current @ $T_C = 100^\circ\text{C}$	40	A
$I_{FM(1)}$	Pulsed Diode Forward Current @ $T_C = 25^\circ\text{C}$	120	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	333	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	166	W
T_J	Operating Junction Temperature	-55 to +175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Notes:

1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC(IGBT)}$	Thermal Resistance, Junction to Case	-	0.45	$^\circ\text{C/W}$
$R_{\theta JC(Diode)}$	Thermal Resistance, Junction to Case	-	0.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGH40T100SMD	FGH40T100SMD	TO-247 A03	-	-	30ea
FGH40T100SMD	FGH40T100SMD-F155	TO-247 G03	-	-	30ea

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	1000	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	-	0.6	-	V/°C
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	1000	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	± 500	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 250\text{ }\mu\text{A}, V_{CE} = V_{GE}$	4.2	5.3	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	-	1.9	2.3	V
		$I_C = 40\text{ A}, V_{GE} = 15\text{ V}, T_C = 175^\circ\text{C}$	-	2.4	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	3980	5295	pF
C_{oes}	Output Capacitance		-	124	165	pF
C_{res}	Reverse Transfer Capacitance		-	76	115	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600\text{ V}, I_C = 40\text{ A}, R_G = 10\text{ }\Omega, V_{GE} = 15\text{ V}, \text{Inductive Load}, T_C = 25^\circ\text{C}$	-	29	38	ns
t_r	Rise Time		-	42	55	ns
$t_{d(off)}$	Turn-Off Delay Time		-	285	371	ns
t_f	Fall Time		-	23	30	ns
E_{on}	Turn-On Switching Loss		-	2.35	3.1	mJ
E_{off}	Turn-Off Switching Loss		-	1.15	1.5	mJ
E_{ts}	Total Switching Loss		-	3.5	4.6	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600\text{ V}, I_C = 40\text{ A}, R_G = 10\text{ }\Omega, V_{GE} = 15\text{ V}, \text{Inductive Load}, T_C = 175^\circ\text{C}$	-	27	36	ns
t_r	Rise Time		-	49	64	ns
$t_{d(off)}$	Turn-Off Delay Time		-	285	371	ns
t_f	Fall Time		-	20	26	ns
E_{on}	Turn-On Switching Loss		-	4.4	5.7	mJ
E_{off}	Turn-Off Switching Loss		-	1.9	2.5	mJ
E_{ts}	Total Switching Loss		-	6.3	8.2	mJ
Q_g	Total Gate Charge	$V_{CE} = 600\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	-	265	398	nC
Q_{ge}	Gate to Emitter Charge		-	32	48	nC
Q_{gc}	Gate to Collector Charge		-	135	203	nC

Electrical Characteristics of Diode $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Unit	
V_{FM}	Diode Forward Voltage	$I_F = 40\text{ A}$	$T_C = 25^\circ\text{C}$	-	3.4	4.4	V
			$T_C = 175^\circ\text{C}$	-	2.6	-	
t_{rr}	Diode Reverse Recovery Time	$I_F = 40\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	60	78	ns
			$T_C = 175^\circ\text{C}$	-	256	-	
Q_{rr}	Diode Reverse Recovery Charge	$I_F = 40\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	185	260	nC
			$T_C = 175^\circ\text{C}$	-	1512	-	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

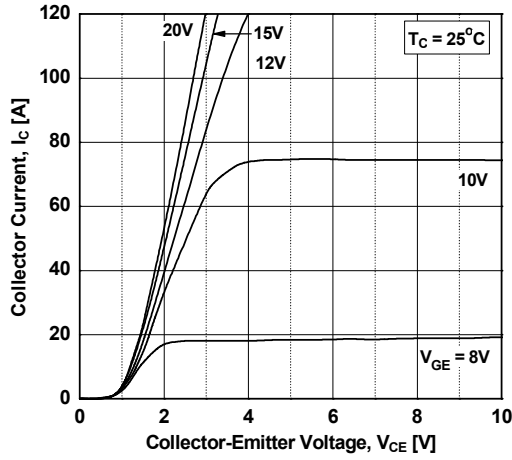


Figure 2. Typical Output Characteristics

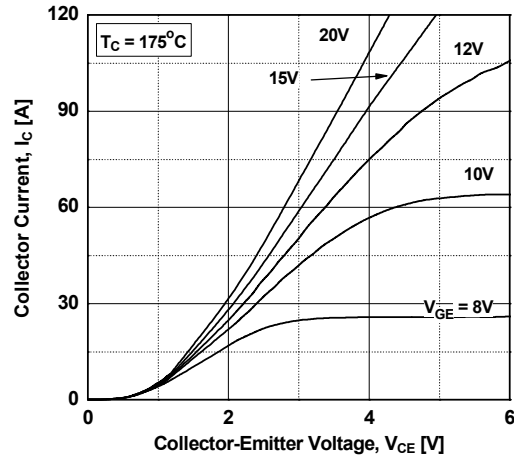


Figure 3. Typical Saturation Voltage Characteristics

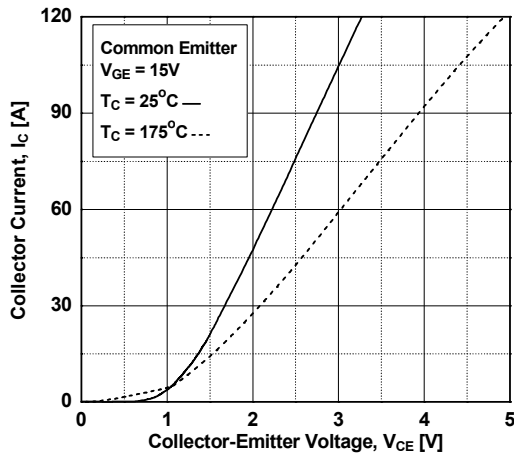


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

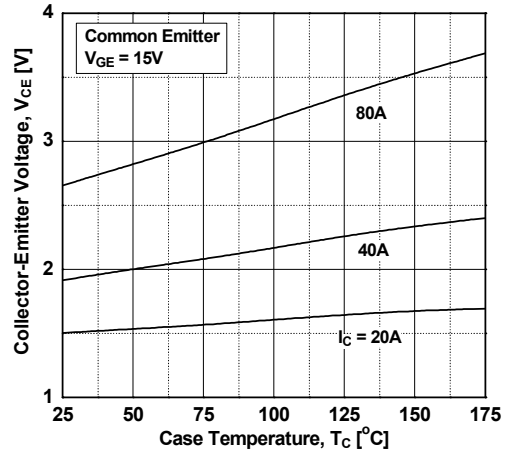


Figure 5. Saturation Voltage vs. Vge

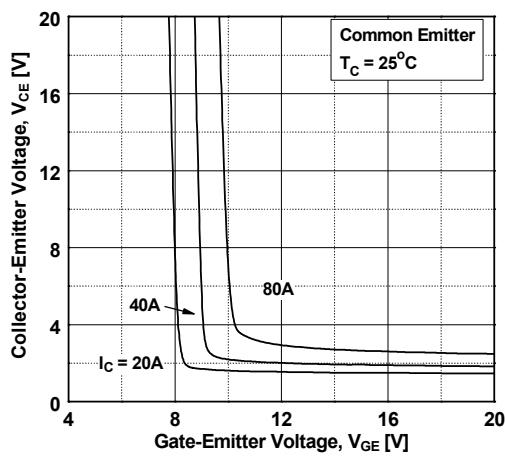
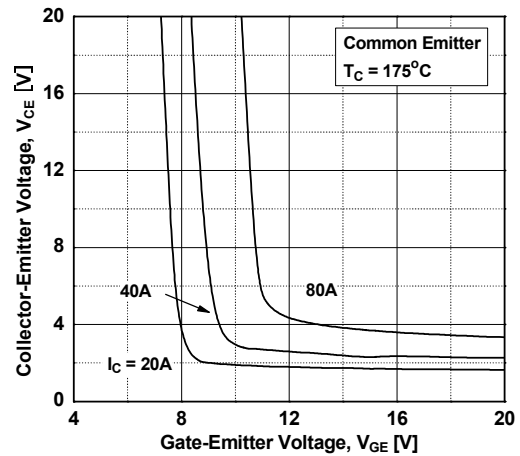


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics

Figure 7. Capacitance Characteristics

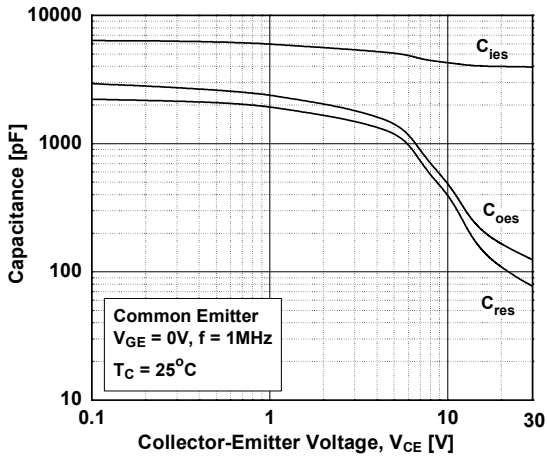


Figure 8. Gate charge Characteristics

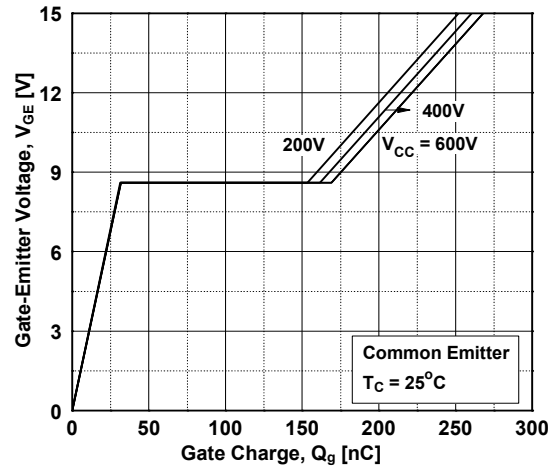


Figure 9. Turn-on Characteristics vs. Gate Resistance

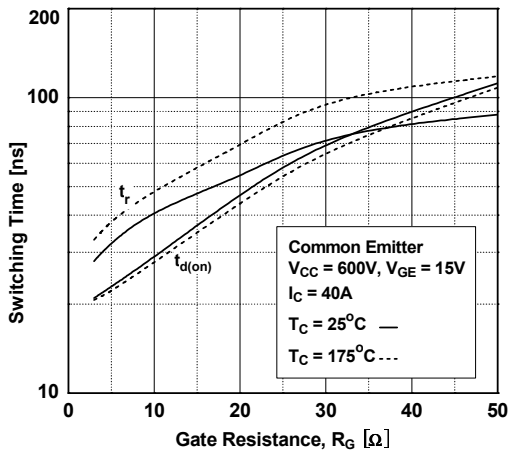


Figure 10. Turn-off Characteristics vs. Gate Resistance

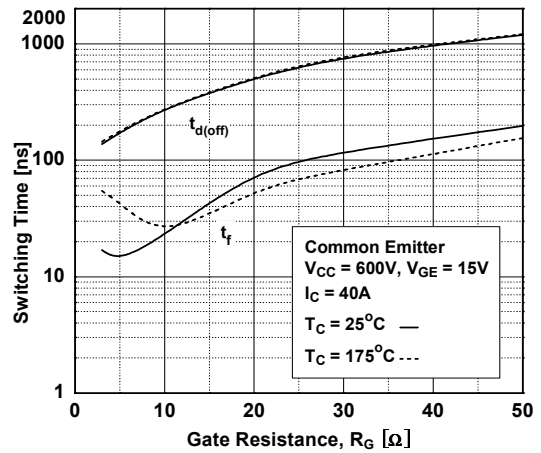


Figure 11. Switching Loss vs. Gate Resistance

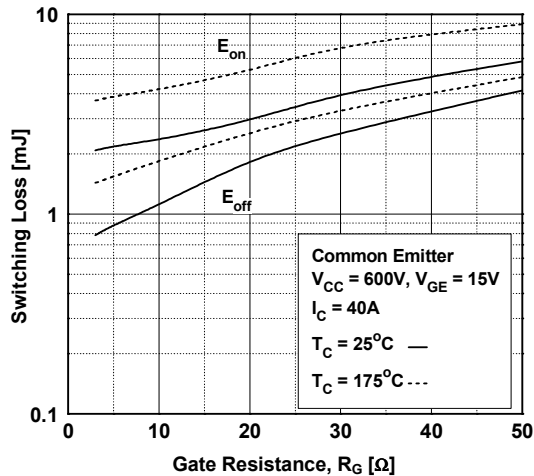
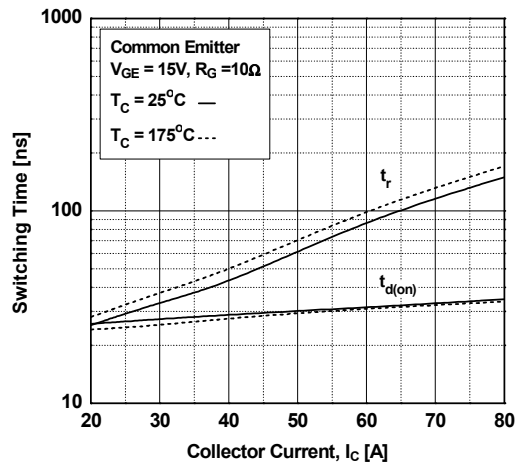


Figure 12. Turn-on Characteristics vs. Collector Current



Typical Performance Characteristics

Figure 13. Turn-off Characteristics vs. Collector Current

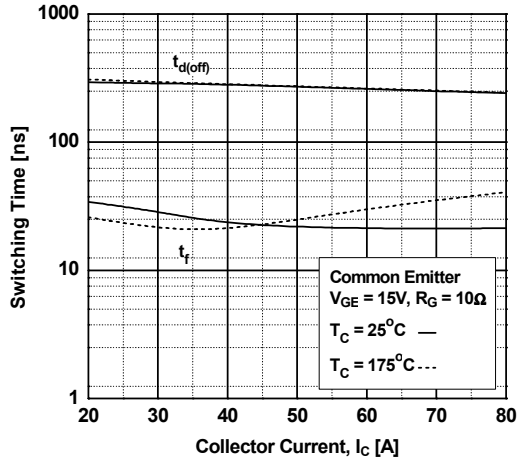


Figure 14. Switching Loss vs. Collector Current

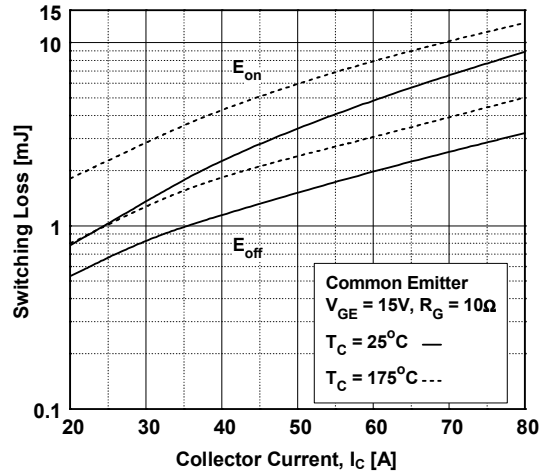


Figure 15. Load Current Vs. Frequency

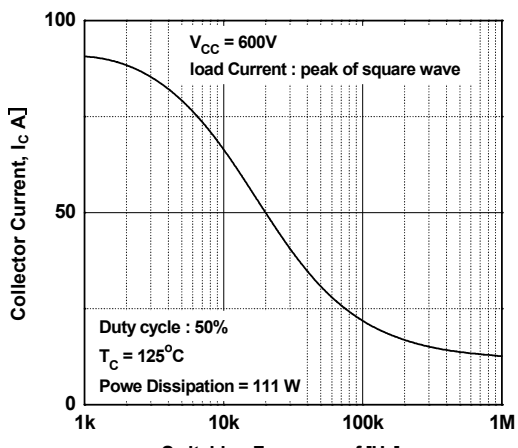


Figure 16. SOA Characteristics

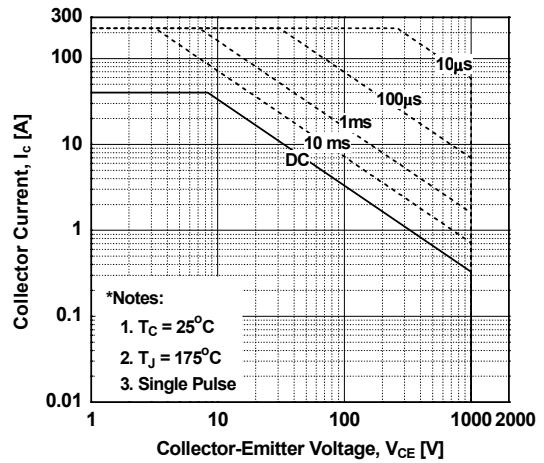


Figure 17. Forward Characteristics

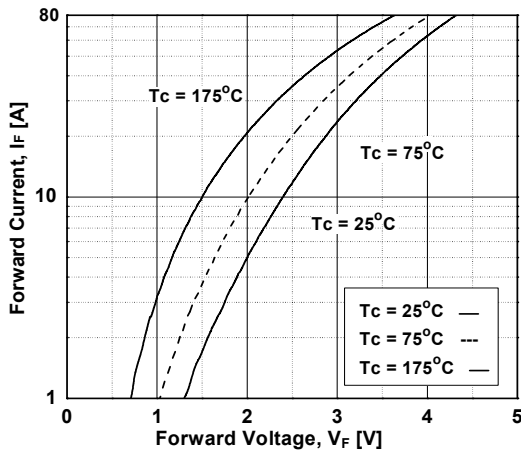
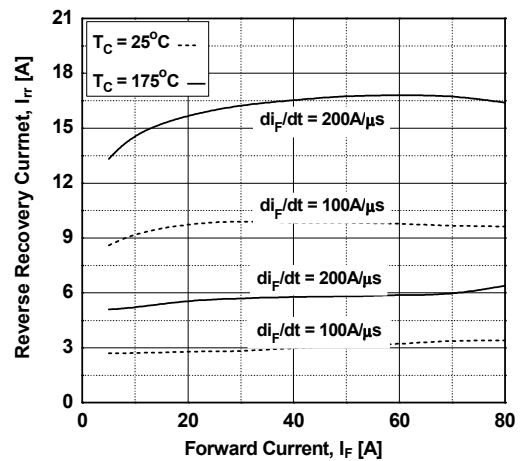


Figure 18. Reverse Recovery Current



Typical Performance Characteristics

Figure 19. Reverse Recovery Time

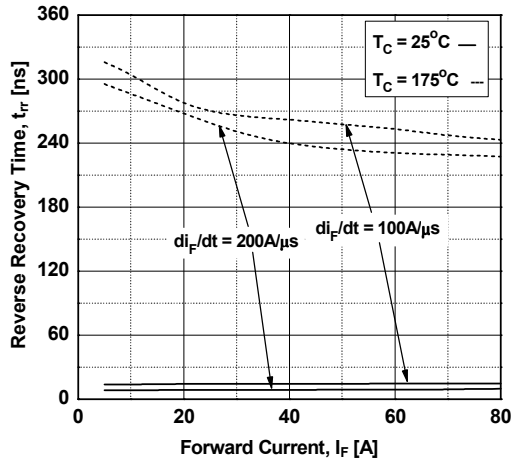


Figure 20. Stored Charge

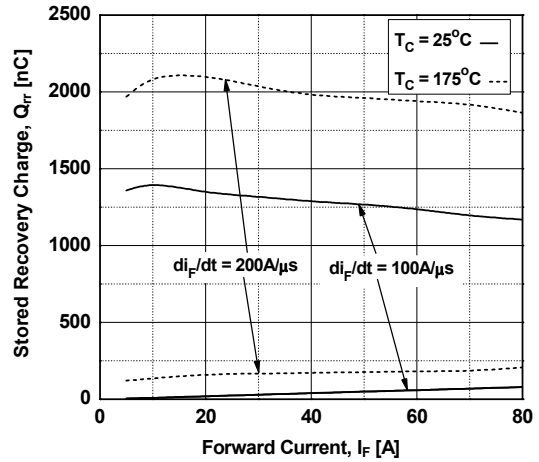


Figure 21. Transient Thermal Impedance of IGBT

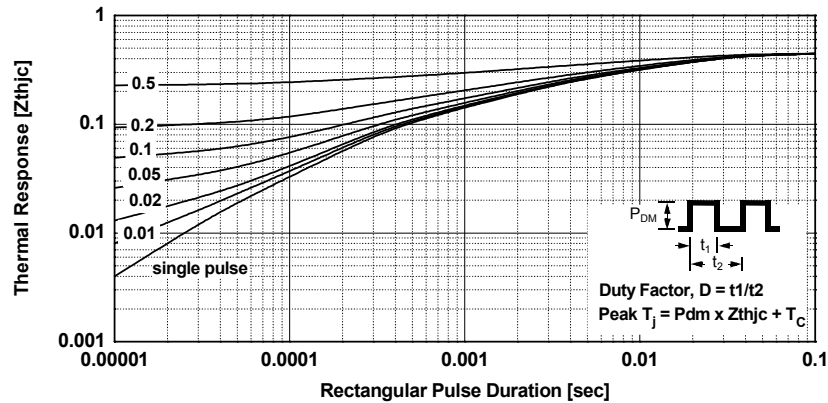
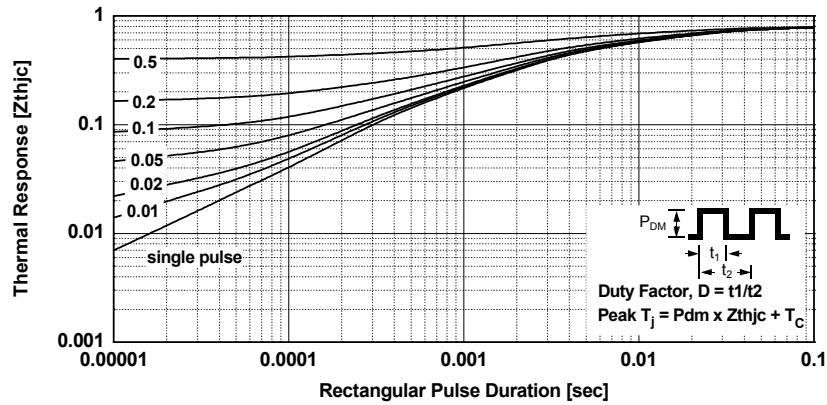
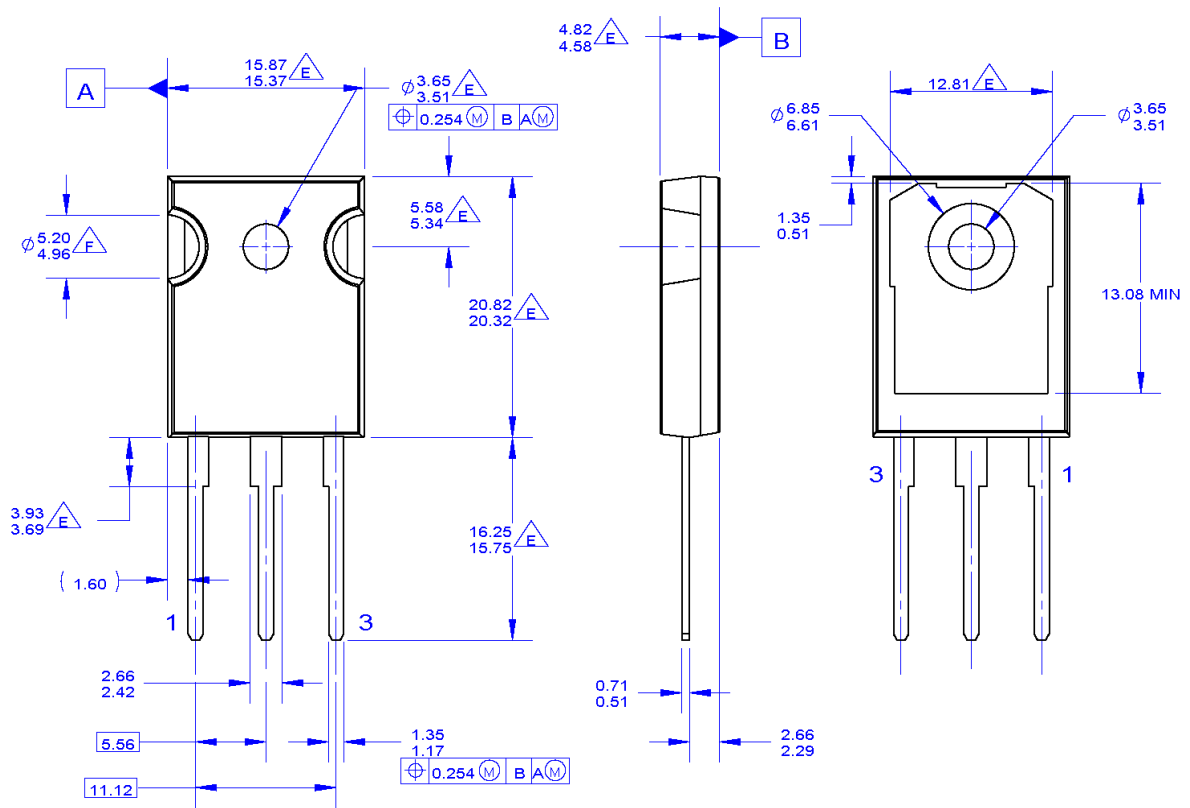


Figure 22. Transient Thermal Impedance of Diode



Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 - 1994

$\triangle E$ DOES NOT COMPLY JEDEC STANDARD VALUE


$\triangle F$ NOTCH MAY BE SQUARE

G. DRAWING FILENAME: MKT-TO247A03_REV03

Figure 23. TO-247, MOLDED, 3 LEAD, JEDEC VARIATION AB (Active)

Package drawings are provided as a service to customers considering ON Semiconductor components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a ON Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of ON Semiconductor's worldwide terms and conditions, specifically the warranty therein, which covers ON Semiconductor products.

Dimensions in Millimeters

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
 USA/Canada

Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910

Japan Customer Focus Center

Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative